

BRMJD44DP

Rev.A Nov.-2023



蓝箭电子
BLUE ROCKET ELECTRONICS

DATA SHEET

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Silicon 4 6 4transistor in a TO-252 Plastic Package.

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@ f Parameter	... Z Symbol	f > Rating	% y Unit
Collector to Base Voltage	V _{CBO}	80	V
Collector to Emitter Voltage	V _{CEO}	80	V
Emitter to Base Voltage	V _{EBO}	5.0	V
Collector Current - Continuous	I _C	8.0	A
Collector Peak Current	I _{CM}	16.0	A
Collector Power Dissipation	P _D (T _A =25 -)	1.75	W
Collector Power Dissipation	P _D (T _C =25 -)	20	W
Junction Temperature	T _J	150	
Storage Temperature Range	T _{stg}	-55 150	

@ f Parameter	... Z Symbol	y i Ú ^ Test Conditions	Â 4 > Min	Á ° > Typ	Â Ý > Max	% y Unit
Collector to Emitter Breakdown Voltage						
Collector Cut-Off Current	I _{CES}	V _{CE} = 80V V _{BE} = 0				

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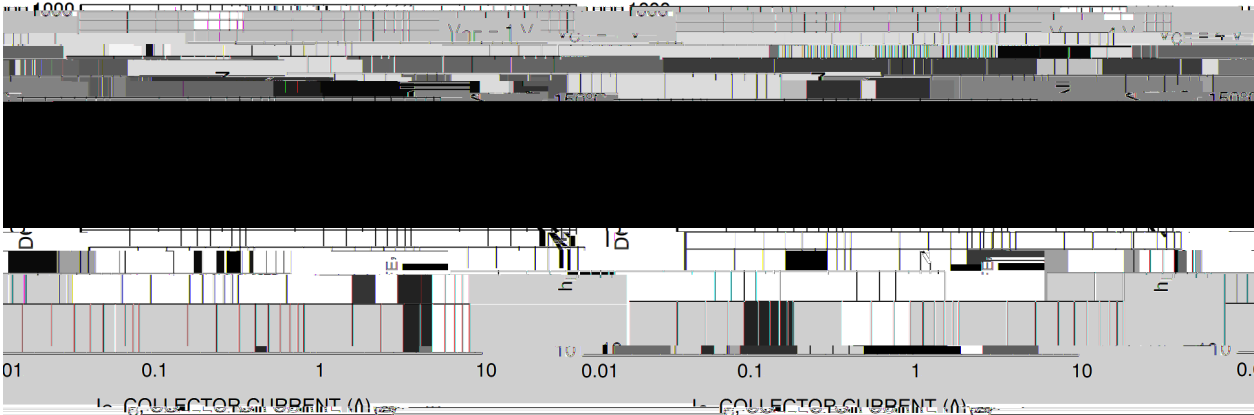
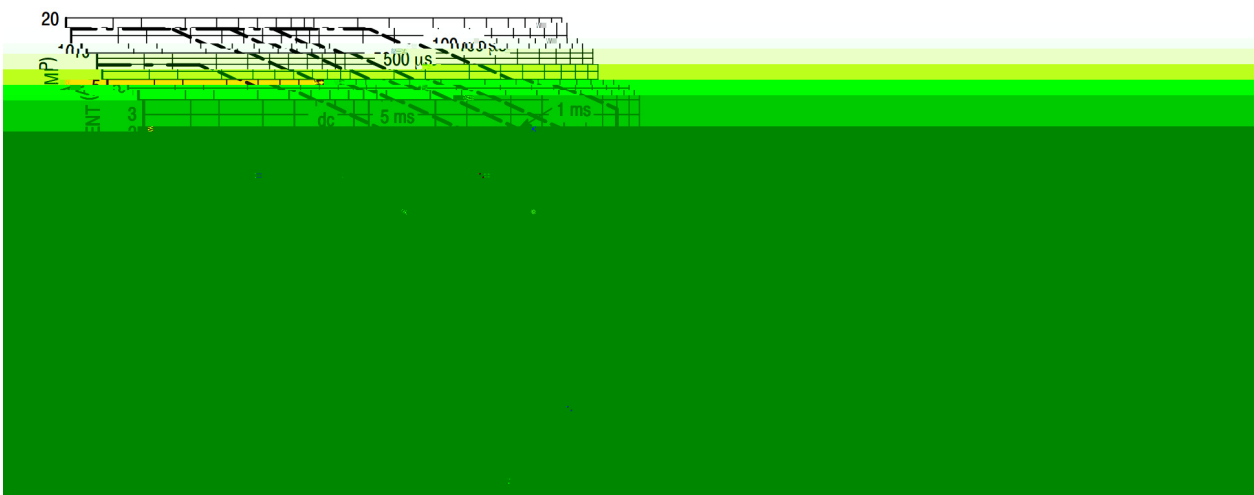
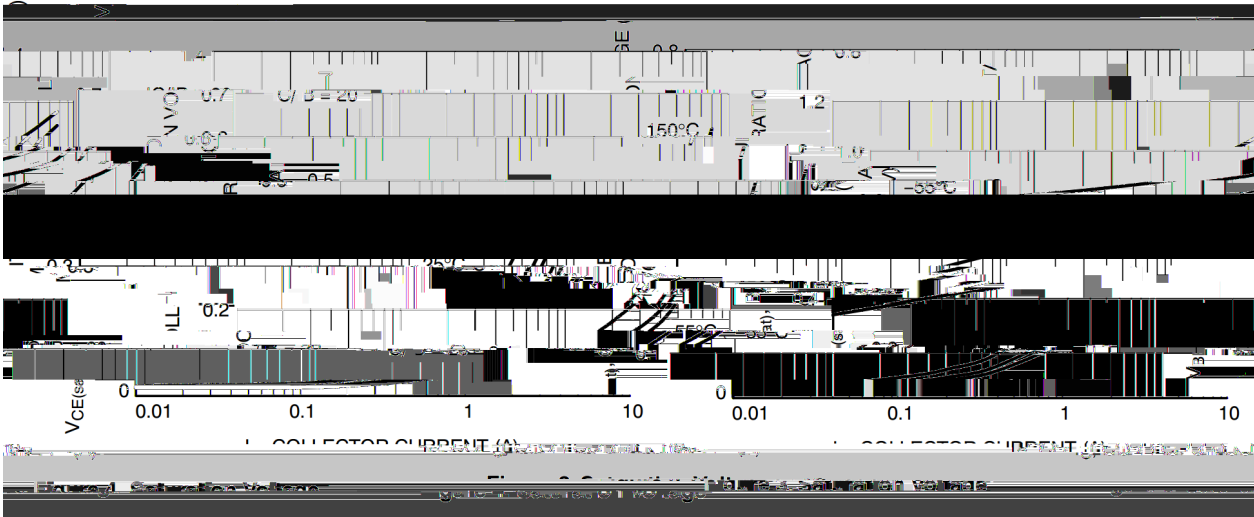
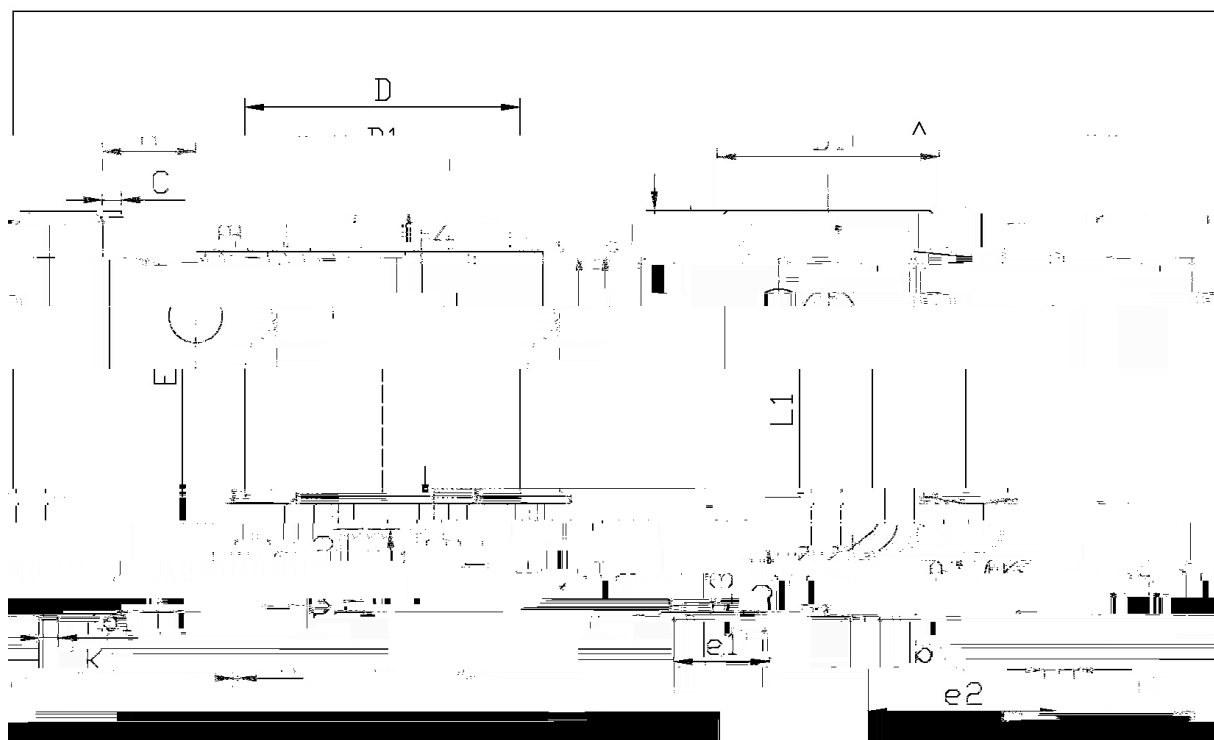


Figure 1. DC Current Gain

Figure 2. DC Current Gain



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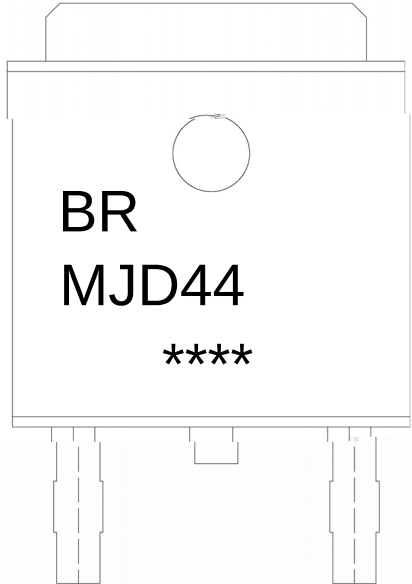


单位: mm

Symbol I		Symbol	
Max	Min	Max	Min
6.25	3.30	2.40	5.95
0.50	0.90	0.20	0.70
0.45	0.55	9.45	9.95
0.60	0.69	0.75	1.20
5.16	5.56	0.00	0.00

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Note:	
BR:	Company Code
MJD44:	Product Type Code
****:	Lot No. Code, code change with Lot No

